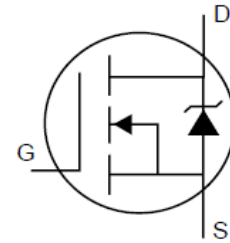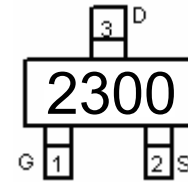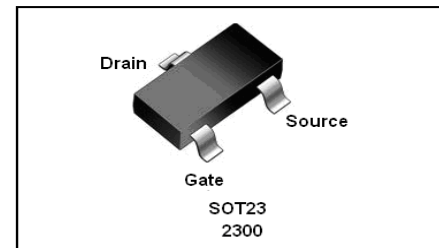## Description

The 2300 designed by the trench processing techniques to achieve extremely low on-resistance. And fast switching speed and improved transfer effective . These features combine to make this design an extremely efficient and reliable device for variety of DC-DC applications.

Features

- ♦ Ron(typ.)=25 mΩ @VGS=2.5V
- ♦ Ron(typ.)=21 mΩ @VGS=4.5V
- ♦ Low On-Resistance
- ♦ 150°C Operating Temperature
- ♦ Fast Switching
- ♦ Lead-Free, RoHS Compliant

Application

- ● Battery protection
- ● Load switch
- ● Power management

Schematic diagram

Marking and pin Assignment

Symbol	Parameter		Rating	Unit
Common Ratings (T$_C$=25°C Unless Otherwise Noted)				
V$_{GS}$	Gate-Source Voltage		±12	V
V$_{(BR)DSS}$	Drain-Source Breakdown Voltage		20	V
T$_J$	Maximum Junction Temperature		150	°C
T$_{STG}$	Storage Temperature Range		-50 to 155	°C
I$_S$	Diode Continuous Forward Current	T$_C$=25°C	5.2[①]	A
Mounted on Large Heat Sink				
I$_{DM}$	Pulse Drain Current Tested	T$_C$=25°C	20	A
I$_D$	Continuous Drain Current(VGS=10V)	T$_C$=25°C	5.2[①]	A
		T$_C$=100°C	4.0	
P$_D$	Maximum Power Dissipation	T$_C$=25°C	1.25	W
R$_{θJA}$	Thermal Resistance Junction-Ambient		135	°C/W

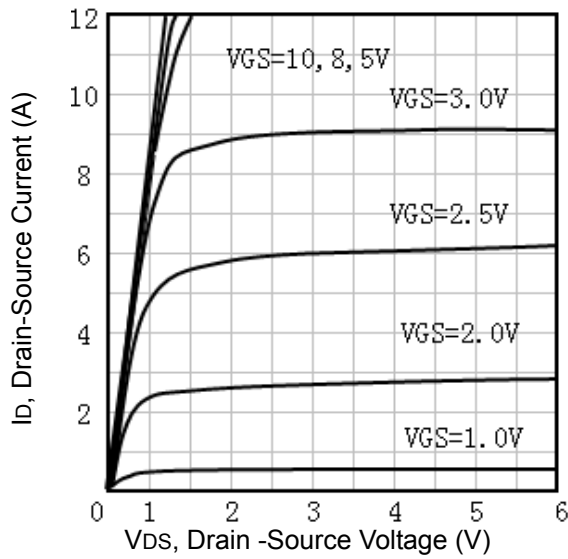| Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T$_J$ = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250µA	20	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current (Tc=25℃)	V_{DS}=20V,V_{GS}=0V	--	--	1	µA
	Zero Gate Voltage Drain Current (Tc=125℃)	V_{DS}=20V,V_{GS}=0V	--	--	100	µA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±12V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250µA	0.5	0.7	1.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=2.5V,I_D=5.2A	--	25	35	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=4.5V, I_D=6A	--	21	25	mΩ
Dynamic Electrical Characteristics @ T$_J$ = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=10V,V_{GS}=0V, f=1MHz	--	630	--	pF
C_{oss}	Output Capacitance		--	150	--	pF
C_{rss}	Reverse Transfer Capacitance		--	60	--	pF
Q_g	Total Gate Charge	V_{DS}=10V,I_D=2.8A, V_{GS}=4.5V	--	11	--	nC
Q_{gs}	Gate-Source Charge		--	1.6	--	nC
Q_{gd}	Gate-Drain Charge		--	2.7	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=10V, I_D=1A, R_G=6Ω, V_{GS}=4.5V, R_L=5Ω,	--	14.5	--	nS
t_r	Turn-on Rise Time		--	46	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	52	--	nS
t_f	Turn-Off Fall Time		--	39	--	nS
Source- Drain Diode Characteristics						
I_{SD}	Source-drain current(Body Diode)	Tc=25℃	--	--	5.2[1]	A
I_{SDM}	Pulsed Source-drain current (Body Diode)		--	--	20[1]	A
V_{SD}	Forward on voltage	Tj=25℃,I_{SD}=2.8A, V_{GS}=0V	--	0.85	1.3	V

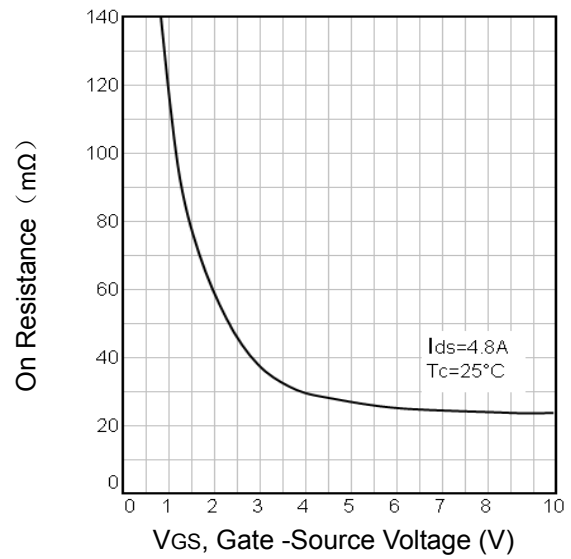## Typical Characteristics

Fig1. Typical Output Characteristics
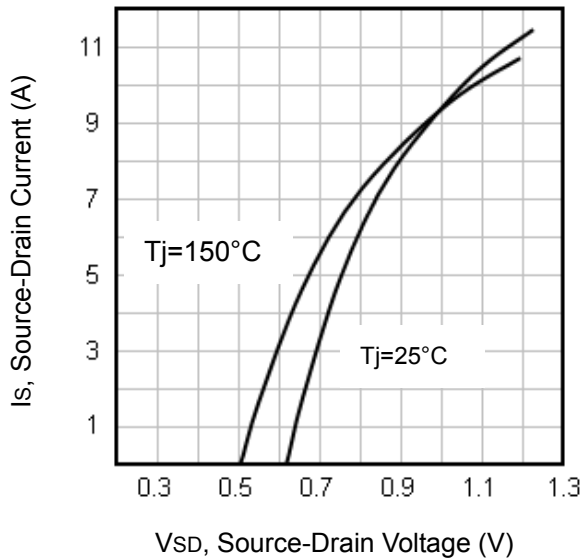
Fig2. Typical Transfer Characteristics
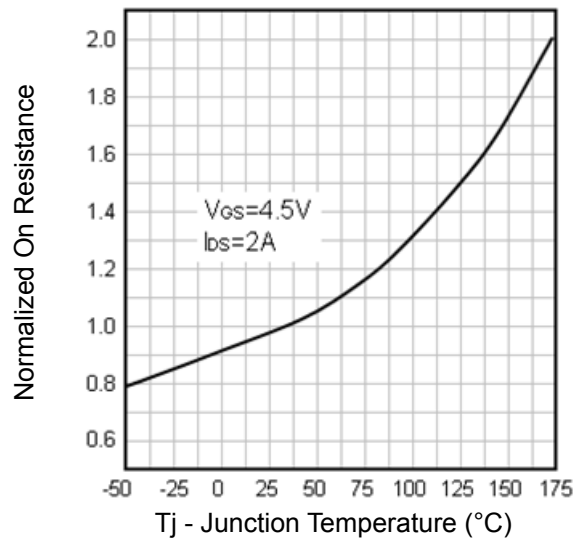
Fig7. Typical Source-Drain Diode Forward Voltage

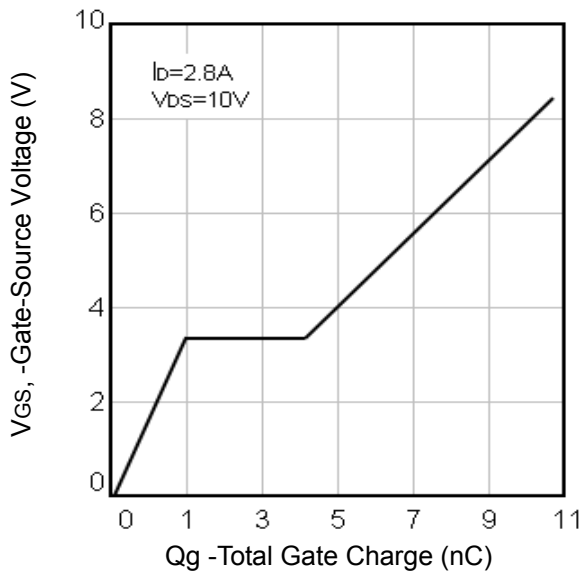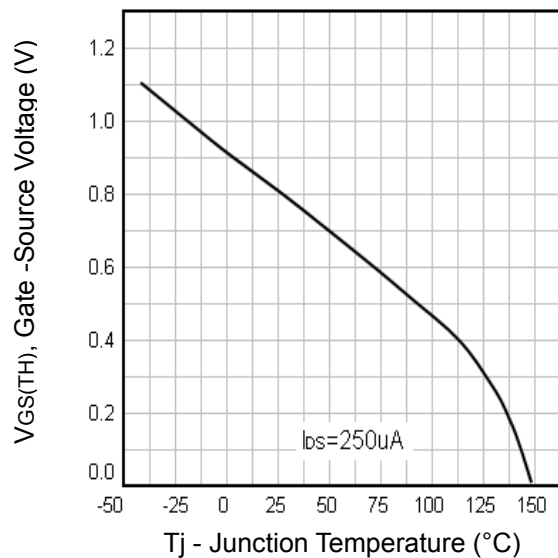Fig4. Normalized On-Resistance Vs. Temperature

Fig5. Typical Gate Charge Vs.Gate-Source Voltage

Fig6. Threshold Voltage Vs. Temperature